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FDMA905P

Single P-Channel PowerTrench® MOSFET -12 V, -10 A, 16 m Ω

Features

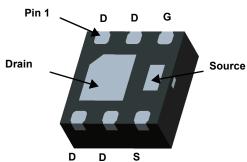
- Max $r_{DS(on)}$ = 16 m Ω at V_{GS} = -4.5 V, I_D = -10 A
- Max $r_{DS(on)}$ = 21 m Ω at V_{GS} = -2.5 V, I_D = -8.9 A
- Max $r_{DS(on)}$ = 82 m Ω at V_{GS} = -1.8 V, I_D = -4.5 A
- Low profile 0.8 mm maximum in the new package MicroFET 2X2 mm
- Free from halogenated compounds and antimony oxides
- RoHS Compliant

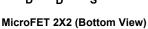


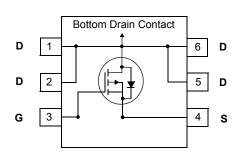
General Description

This device is designed specifically for battery charge or load switching in cellular handset and other ultraportable applications. It features a MOSFET with low on-state resistance.

The MicroFET 2X2 package offers exceptional thermal performance for its physical size and is well suited to linear mode applications.







MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DS}	Drain to Source Voltage		-12	V
V_{GS}	Gate to Source Voltage		±8	V
	Drain Current -Continuous	(Note 1a)	-10	۸
'D	-Pulsed		-40	A
D	Power Dissipation	(Note 1a)	2.4	W
P_{D}	Power Dissipation	(Note 1b)	0.9	VV
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	6.9	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	52	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	145	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
A95	FDMA905P	MicroFET 2X2	7 "	8 mm	3000 units

Electrical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units		
Off Characteristics								
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = -250 \mu A, V_{GS} = 0V$	-12			V		
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = -250 μA, referenced to 25 °C		-4.3		mV/°C		
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -9.6 V, V _{GS} = 0 V			-1	μΑ		
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA		

On Characteristics

V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_{D} = -250 \mu A$	-0.4	-0.7	-1.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = -250 μ A, referenced to 25 °C		2.6		mV/°C
	Static Drain to Source On Resistance	$V_{GS} = -4.5 \text{ V}, I_D = -10 \text{ A}$		14	16	mΩ
		$V_{GS} = -2.5 \text{ V}, I_D = -8.9 \text{ A}$		17	21	
r _{DS(on)}		V _{GS} = -1.8 V, I _D = -4.5 A		21	82	
		$V_{GS} = -4.5 \text{ V}, I_D = -10 \text{ A}, T_J = 125 ^{\circ}\text{C}$		16	21	Ī
g _{FS}	Forward Transconductance	V _{DD} = -5 V, I _D = -10 A		50		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V - CV V - OV	2559	3405	pF
Coss	Output Capacitance	$V_{DS} = -6 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz	490	735	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 1/11/12	437	655	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time		11	20	ns
t _r	Rise Time	$V_{DD} = -6 \text{ V}, I_{D} = -10 \text{ A},$	11	20	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = -4.5 V, R_{GEN} = 6 Ω	120	192	ns
t _f	Fall Time		59	94	ns
Q_g	Total Gate Charge	V - CV I - 40 A	21	29	nC
Q_{gs}	Gate to Source Charge	V _{DD} = -6 V, I _D = -10 A, V _{GS} = -4.5 V	3.5		nC
Q_{qd}	Gate to Drain "Miller" Charge	VGS4.5 V	4.2		nC

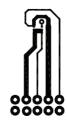
Drain-Source Diode Characteristics

V _{SD}	1Source to Drain Dioge Forward Voltage	$V_{GS} = 0 \text{ V, } I_{S} = -2 \text{ A}$	(Note 2)	-0.6	-1.2	V
		$V_{GS} = 0 \text{ V}, I_{S} = -10 \text{ A}$	(Note 2)	-0.8	-1.2	
t _{rr}	Reverse Recovery Time	-I _F = -10 A, di/dt = 100 A/μs		21	34	ns
Q _{rr}	Reverse Recovery Charge			6.1	12	nC

Notes: 1. $R_{\theta,JR}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta,JC}$ is guaranteed by design while $R_{\theta,CA}$ is determined by the user's board design.



a. 52 °C/W when mounted on a 1 in² pad of 2 oz copper.



b. 145 °C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 $\mu\text{s},$ Duty cycle < 2.0 %.

Typical Characteristics T_J = 25 °C unless otherwise noted

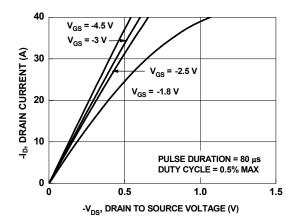


Figure 1. On-Region Characteristics

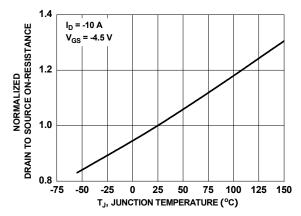


Figure 3. Normalized On-Resistance vs Junction Temperature

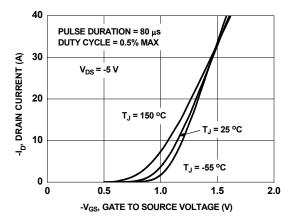


Figure 5. Transfer Characteristics

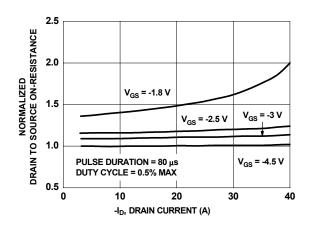


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

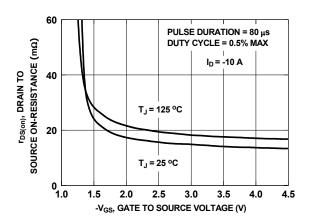


Figure 4. On-Resistance vs Gate to Source Voltage

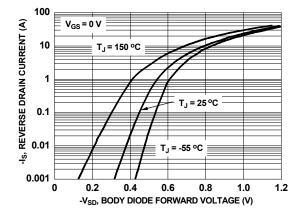


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25 °C unless otherwise noted

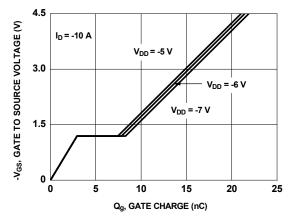


Figure 7. Gate Charge Characteristics

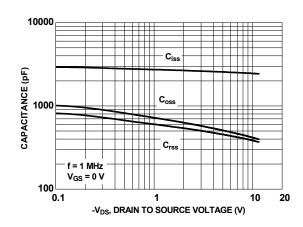


Figure 8. Capacitance vs Drain to Source Voltage

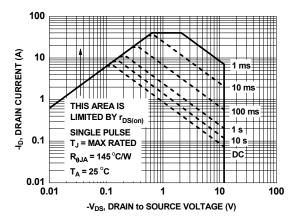


Figure 9. Forward Bias Safe Operating Area

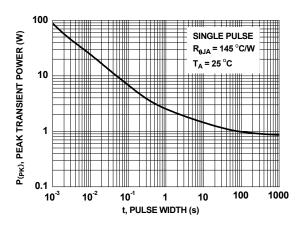


Figure 10. Single Pluse Maximum Power Dissipation

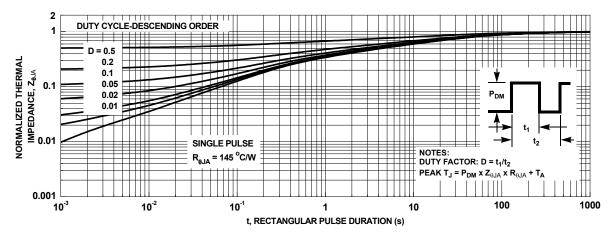
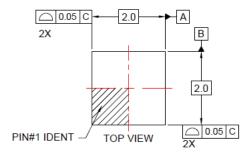
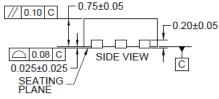
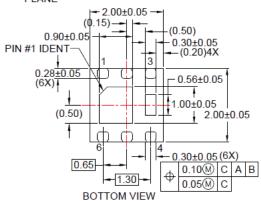


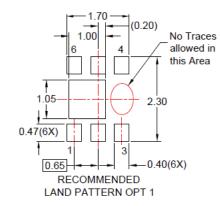
Figure 11. Junction-to-Ambient Transient Thermal Response Curve

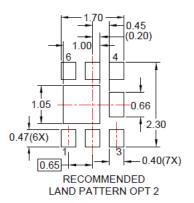
Dimensional Outline and Pad Layout











NOTES:

- A. PACKAGE DOES NOT FULLY CONFORM TO JEDEC MO-229 REGISTRATION
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.
- E. DRAWING FILENAME: MKT-MLP06Lrev4.

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